

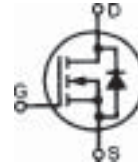
High Voltage MOSFET

N-Channel Enhancement Mode
Avalanche Energy Rated

Preliminary Data

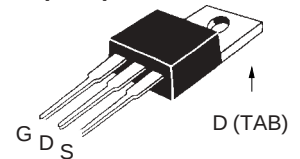
IXTA 1N80
IXTP 1N80
IXTY 1N80

$V_{DSS} = 800 \text{ V}$
 $I_{D25} = 750 \text{ mA}$
 $R_{DS(on)} = 11 \Omega$

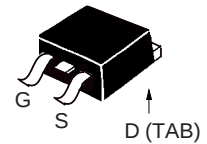


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	800	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	800	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	750	mA
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	3	A
I_{AR}		1.0	A
E_{AR}	$T_C = 25^\circ\text{C}$	5	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	100	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 47 \Omega$	3	V/ns
P_D	$T_C = 25^\circ\text{C}$	40	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-220	4	g
	TO-252	0.8	g
	TO-263	3	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

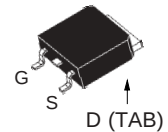
TO-220AB (IXTP)



TO-263 AA (IXTA)



TO-252 AA (IXTY)



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- High voltage, Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Fast switching times

Applications

- Switch-mode and resonant-mode power supplies
- Flyback inverters
- DC choppers
- High frequency matching

Advantages

- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 25 \mu\text{A}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		25 μA
		$T_J = 125^\circ\text{C}$		500 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 500 \text{ mA}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$	9.5	11	Ω

Symbol	Test Conditions	Characteristic Values (T _j = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 20\text{ V}; I_D = 500\text{ mA}$, pulse test	0.7	0.8	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		220	pF
C_{oss}			23	pF
C_{rss}			4	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 1\text{ A}$ $R_G = 47\Omega$, (External)		11	ns
t_r			19	ns
$t_{d(off)}$			40	ns
t_f			28	ns
$Q_{G(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 1\text{ A}$		8.5	nC
Q_{GS}			2.5	nC
Q_{GD}			4.5	nC
R_{thJC}				3.1 K/W
R_{thCK}	(IXTP)		0.50	K/W

Source-Drain Diode		Characteristic Values (T _j = 25°C, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			750 mA
I_{SM}	Repetitive; pulse width limited by T _{JM}			3 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$		1.8	2 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		710	ns

TO-252 AA Outline

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.19	2.38	0.086	0.094
A1	0.89	1.14	0.035	0.045
A2	0	0.13	0	0.005
b	0.64	0.89	0.025	0.035
b1	0.76	1.14	0.030	0.045
b2	5.21	5.46	0.205	0.215
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.32	5.21	0.170	0.205
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.170	0.205
e	2.28 BSC		0.090 BSC	
e1	4.57 BSC		0.180 BSC	
H	9.40	10.42	0.370	0.410
L	0.51	1.02	0.020	0.040
L1	0.64	1.02	0.025	0.040
L2	0.89	1.27	0.035	0.050
L3	2.54	2.92	0.100	0.115

TO-220 AD Dimensions

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

TO-263 AA Outline

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54 BSC		.100 BSC	
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	